

Mark: 2J

PNP Switching Transistor

This device is designed for very high speed saturated switching at collector currents to 100 mA. Sourced from Process 65. See PN4258 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	12	V
V _{CBO}	Collector-Base Voltage	12	V
V _{EBO}	Emitter-Base Voltage	4.0	V
Ic	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations. 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics

Symbol	Characteristic	Max U		Units
		PN3640	*MMBT3640	
P _D	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

TA = 25°C unless otherwise noted

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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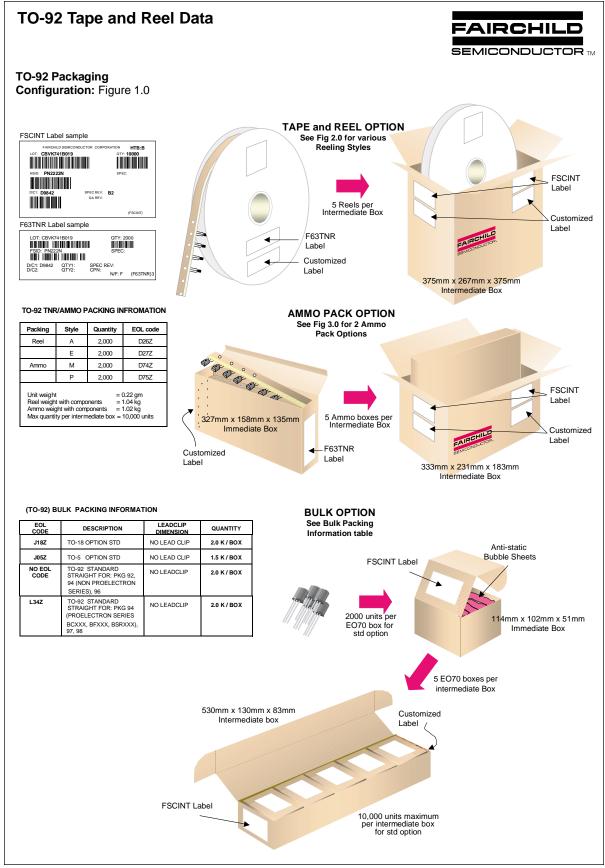
PNP Switching Transistor (continued)

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PN3640 / MMBT3640

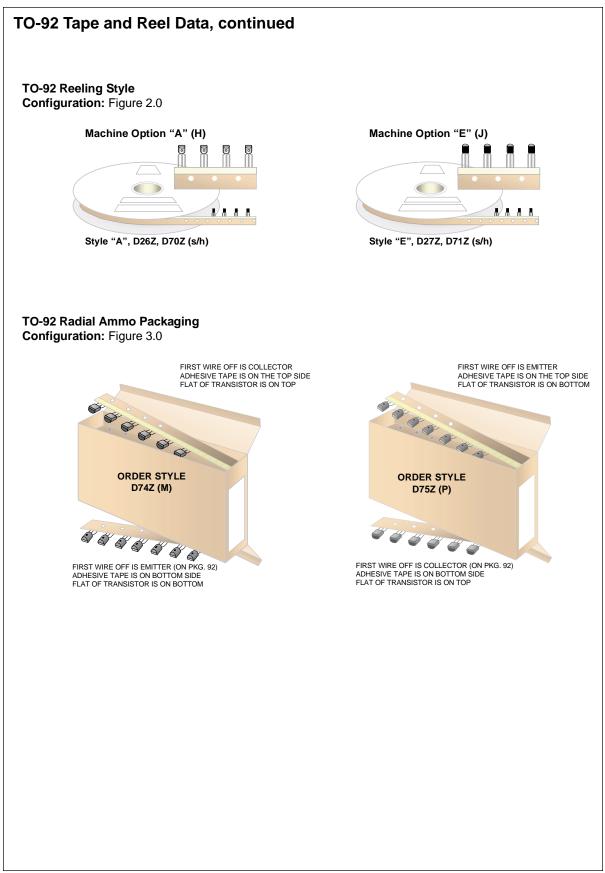
Symbol	Parameter	Test Conditions	Min	Max	Unit
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	12		V
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_{C} = 100 \ \mu A, \ V_{BE} = 0$	12		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	12		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \ \mu A, I_C = 0$	4.0		V
I _{CES}	Collector Cutoff Current	$V_{CE} = 6.0 \text{ V}, V_{BE} = 0$		0.01	μΑ
	Base Current	$V_{CE} = 6.0 \text{ V}, V_{BE} = 0, T_A = 65^{\circ}\text{C}$ $V_{CE} = 6.0 \text{ V}, V_{BE} = 0$		1.0 10	μA nA
В	Dase ourient	V _{CE} = 0.0 V, V _{BE} = 0		10	ПА
ON CHAR	ACTERISTICS*				
h _{FE}	DC Current Gain	$I_{\rm C} = 10 \text{ mA}, V_{\rm CE} = 0.3 \text{ V}$	30	120	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{C} = 50 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$	20	0.3	V
V CE(sat)	Concetor Emilier Galdration Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.0$ mA		0.2	v
		$I_{\rm C} = 50$ mA, $I_{\rm B} = 5.0$ mA		0.6	V
				0.25	V
.,		$I_{C}= 10 \text{ mA}, I_{B}= 1.0 \text{ mA}, T_{A}=65^{\circ}\text{C}$	0.75	0.25	
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.5$ mA	0.75	0.95	V
	Base-Emitter Saturation Voltage		0.75 0.8		
SMALL SI		$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$		0.95 1.0	V V
SMALL SI	GNAL CHARACTERISTICS	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	0.95 1.0	V V V
SMALL SI f _T C _{obo}	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 100 \text{ MHz}$	0.8	0.95 1.0 1.5	V V V
SMALL SI f _T C _{obo}	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	0.95 1.0 1.5 3.5	V V V MHz pF
SMALL SI f _T C _{obo} C _{ibo}	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	0.95 1.0 1.5 3.5	V V V MHz pF
SMALL SI f _T C _{obo} C _{ibo} SWITCHII	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	0.95 1.0 1.5 3.5	V V V MHz pF
SMALL SI f _T C _{obo} C _{ibo} SWITCHII	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	0.95 1.0 1.5 3.5 3.5	V V V MHz pF
SMALL SI f _T C _{obo} C _{ibo} SWITCHII t _d	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	0.95 1.0 1.5 3.5 3.5 10	V V V MHz pF pF
$\frac{\text{SMALL SI}}{f_{T}}$ C_{obo} C_{ibo} $\frac{\text{SWITCHII}}{t_{d}}$ $\frac{t_{d}}{t_{r}}$ t_{s}	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	0.95 1.0 1.5 3.5 3.5 10 30	V V V MHz pF pF
SMALL SI f_T C_{obo} C_{ibo} SWITCHII t_d t_r t_s t_f	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{split}$	0.8	0.95 1.0 1.5 3.5 3.5 10 30 20	V V V V MHz pF pF pF
SMALL SI f _T C _{obo} C _{ibo} SWITCHII t _d t _r t _s t _f	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time	$\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$	0.8	0.95 1.0 1.5 3.5 3.5 3.5 10 30 20 12	V V V PF pF ns ns ns ns
SMALL SI f _T C _{obo} C _{ibo} SWITCHII t _d t _r t _s t _f	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time	$\begin{split} I_{C} &= 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} &= 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} &= 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \\ \end{split}$	0.8	0.95 1.0 1.5 3.5 3.5 3.5 10 30 20 12	V V V PF pF ns ns ns ns
SMALL SI f_T C_{obo} C_{ibo} SWITCHII t_d t_r t_s t_f	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time	$\begin{array}{c} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \\ \end{array}$	0.8	0.95 1.0 1.5 3.5 3.5 10 30 20 12 25	V V V V PF pF ns ns ns ns ns
SMALL SI f _T Cobo Cibo SWITCHII td tr ts tr ts tf ton	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time	$\begin{array}{c} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$	0.8	0.95 1.0 1.5 3.5 3.5 10 30 20 12 25	V V V V PF pF ns ns ns ns ns
SMALL SI f _T Cobo Cibo SWITCHII td tr ts tr ts tf ton	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time Turn-On Time	$\begin{array}{l} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \\ \end{array}$	0.8	0.95 1.0 1.5 3.5 3.5 10 30 20 12 25 60	V V V V V V V V V V V V V V V V V V V
f _T C _{obo} C _{ibo}	GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time Turn-On Time	$\begin{array}{c} I_{C} = 10 \text{ mA}, I_{B} = 0.5 \text{ mA} \\ I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA} \\ I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA} \end{array}$	0.8	0.95 1.0 1.5 3.5 3.5 10 30 20 12 25 60	V V V V V V V V V V V V V V V V V V V

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

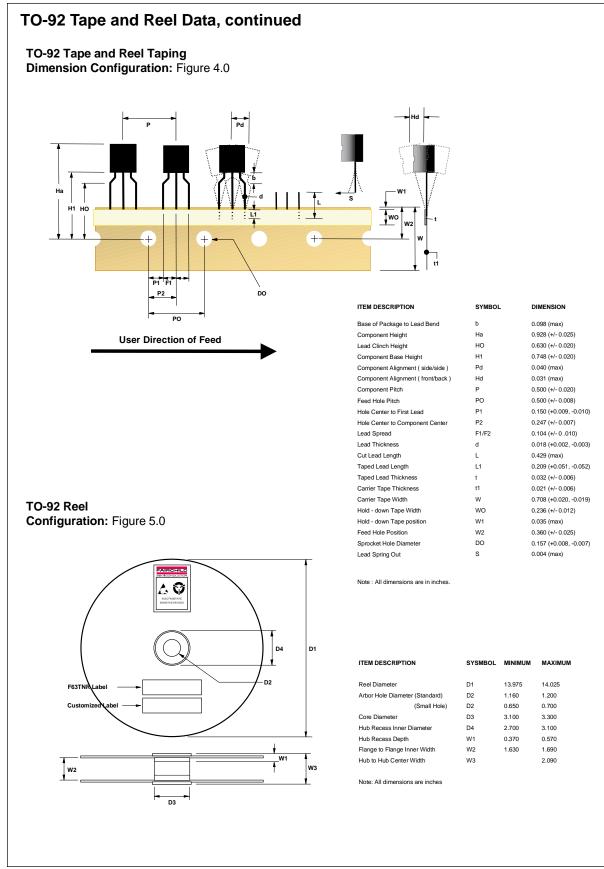


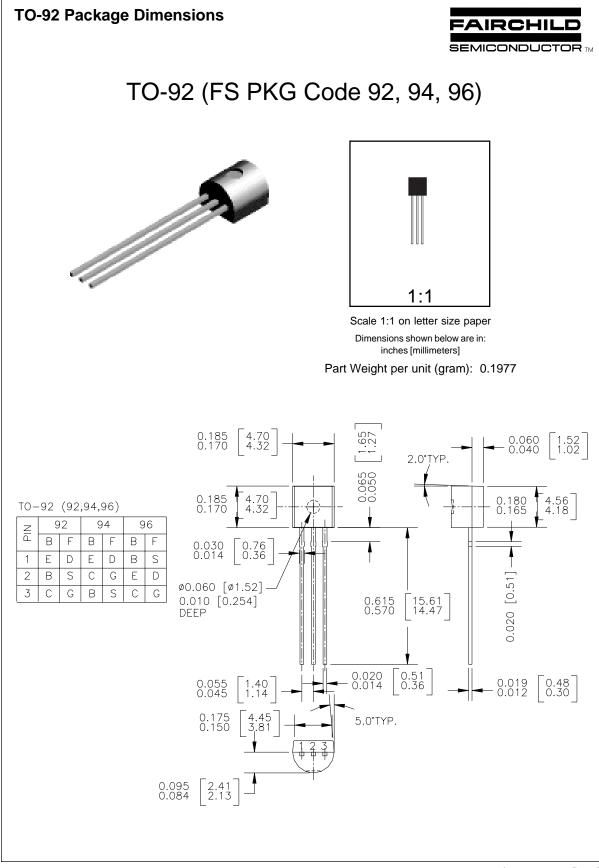
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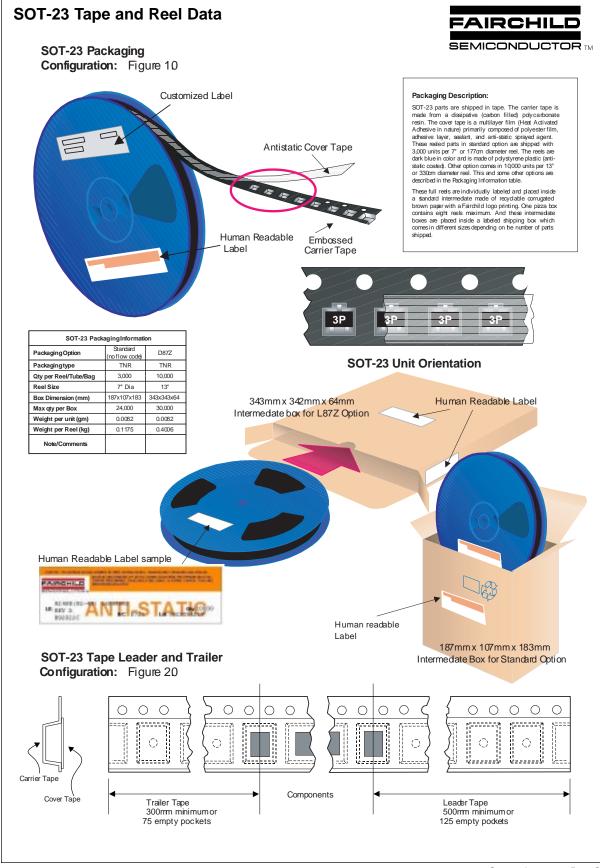
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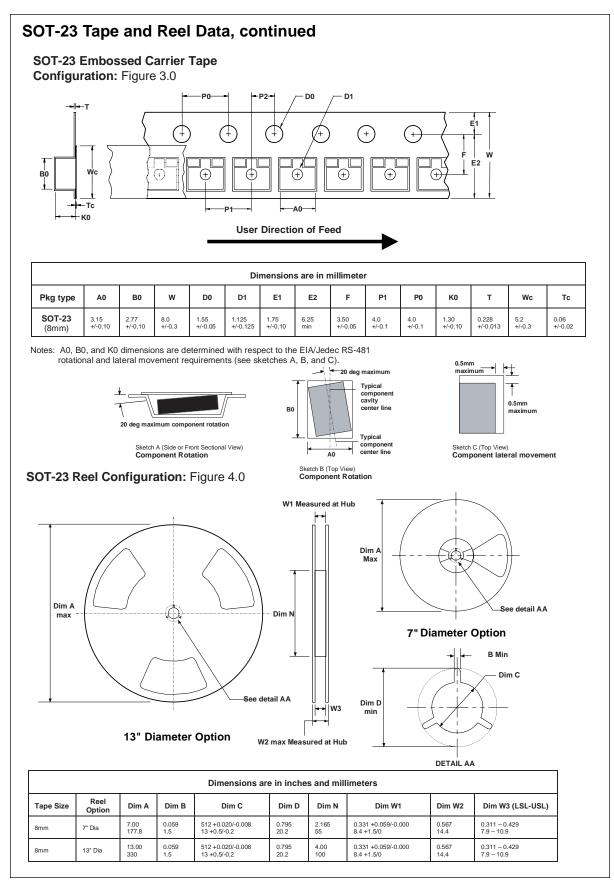
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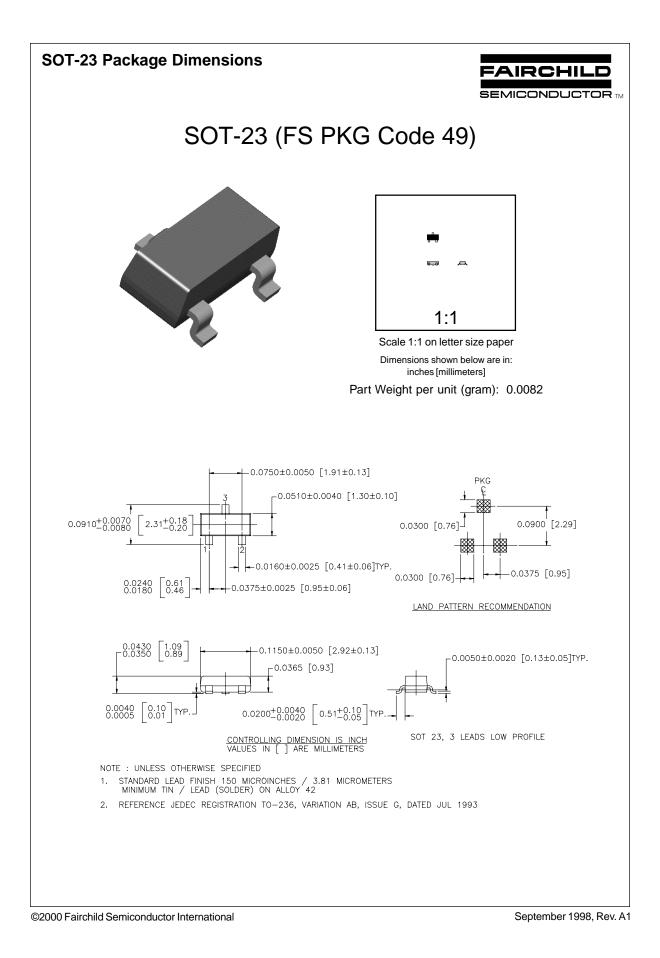


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Definition of Terms

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